

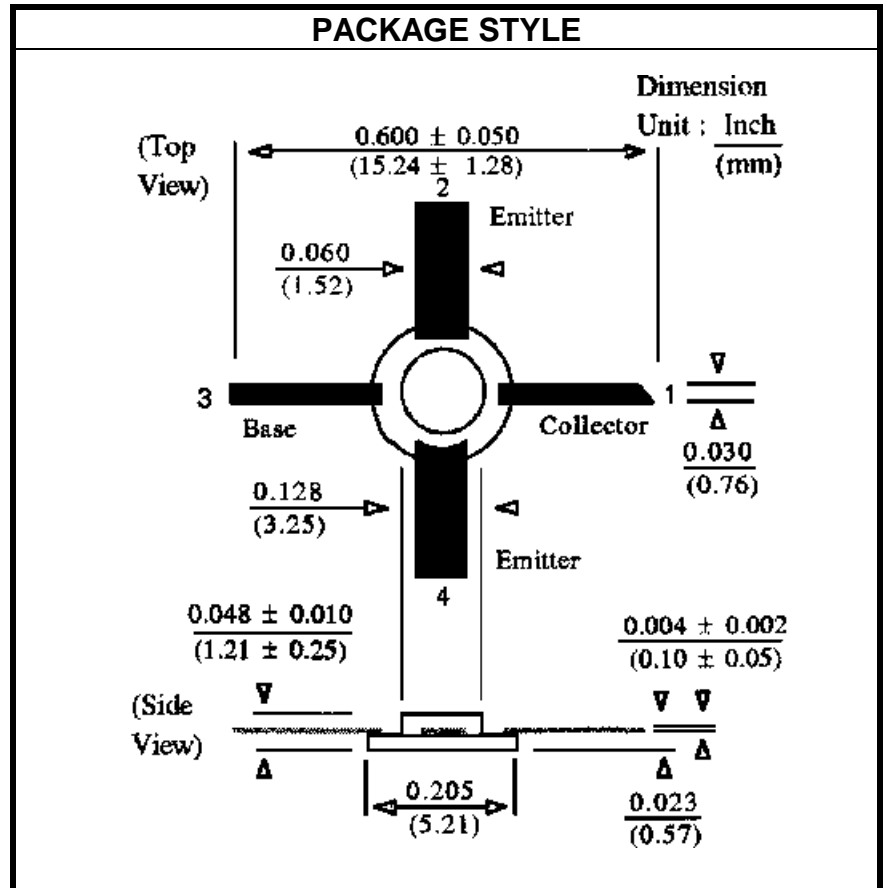
# NPN SILICON RF TRANSISTOR

**DESCRIPTION:**

The **AT64020** is a Common Emitter Device Designed for Medium Power Class C Applications Operating at VHF,UHF Frequencies.

**MAXIMUM RATINGS**

$I_C$	120 mA
$I_C$	180 mA (MAX)
$V_{CEO}$	15 V
$V_{CBO}$	25 V
$V_{EBO}$	1.5 V
$T_J$	200 °C
$T_{STG}$	-65 °C to +150 °C


**CHARACTERISTICS**  $T_C = 25\text{ }^\circ\text{C}$ 

SYMBOL	TEST CONDITIONS			MINIMUM	TYPICAL	MAXIMUM	UNITS
$I_{CBO}$	$V_{CB} = 10\text{ V}$					400	$\mu\text{A}$
$h_{FE}$	$V_{CE} = 8.0\text{ V}$	$I_C = 15\text{ mA}$		30	110	300	---
$f_t$	$V_{CE} = 10\text{ V}$	$I_C = 60\text{ mA}$	$f = 1.0\text{ GHz}$		8.0		GHz
$ S_{21} ^2$	$V_{CE} = 10\text{ V}$	$I_C = 60\text{ mA}$	$f = 1.0\text{ GHz}$		15.6		dB
$ S_{21} ^2$	$V_{CE} = 10\text{ V}$	$I_C = 60\text{ mA}$	$f = 2.0\text{ GHz}$		9.0		dB
$P_{1dB}$	$V_{CE} = 10\text{ V}$	$I_C = 75\text{ mA}$	$f = 1.0\text{ GHz}$		27		dBm
NF	$V_{CE} = 8.0\text{ V}$	$I_C = 20\text{ mA}$	$f = 1.0\text{ GHz}$		1.6		dB